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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	10/627,218
Filing Date	July 25, 2003
First Named Inventor	Yeo, *et al.*
Art Unit	2831
Examiner Name	Ha
Attorney Docket Number	TSM03-0556

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number - Kind Code[2] (*if known*)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
[illegible]	1	US- 2004/0026765 A1	02-12-2004	Currie, et al.	

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Examiner Signature	[signature]	Date Considered	11/3/04

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

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